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PPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.	
10/711,644	09/29/2004	Wei Lu	FIS920040037US1 5643		
29371 75	590 05/01/2006	EXAMINER			
CANTOR COLBURN LLP - IBM FISHKILL			YANTORNO, JENNIFER M		
55 GRIFFIN ROBLOOMFIELD			ART UNIT PAPER NUMBER		
	,		2881		
			DATE MAILED: 05/01/2006	6	

Please find below and/or attached an Office communication concerning this application or proceeding.

	•	Applicatio	n No.	Applicant(s)		
Office Action Summary		10/711,64	4	LU, WEI		
		Examiner		Art Unit		
	•	Jennifer Ya	intorno	2881		
Th	e MAILING DATE of this communicat	ion appears on the	cover sheet with the c	orrespondence address		
A SHORT WHICHE  - Extensions after SIX (6) - If NO perior - Failure to re	ENED STATUTORY PERIOD FOR VER IS LONGER, FROM THE MAIL of time may be available under the provisions of 37 MONTHS from the mailing date of this communicated for reply is specified above, the maximum statutor eply within the set or extended period for reply will, beceived by the Office later than three months after the ent term adjustment. See 37 CFR 1.704(b).	ING DATE OF THE CFR 1.136(a). In no ever ation.  Try period will apply and will by statute, cause the application.	IS COMMUNICATION of, however, may a reply be time expire SIX (6) MONTHS from cation to become ABANDONE	l. ely filed the mailing date of this communication (35 U.S.C. § 133).		
Status						
2a)	sponsive to communication(s) filed of action is <b>FINAL</b> . 2b)[see this application is in condition for seed in accordance with the practice uses.	☐ This action is not allowance except f	for formal matters, pro		S.	
Disposition of	of Claims					
4a) ( 5) ☐ Cla 6) ☑ Cla 7) ☐ Cla 8) ☐ Cla Application I 9) ☐ The	specification is objected to by the E	vithdrawn from con n and/or election re xaminer.	quirement.	ad to butho Everyiner		
App Rep	drawing(s) filed on 18 November 20 licant may not request that any objection lacement drawing sheet(s) including the oath or declaration is objected to by	n to the drawing(s) be correction is require	e held in abeyance. Seed of the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 CFR 1.121(d	ರ).	
Priority unde	er 35 U.S.C. § 119					
<ul> <li>12) Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).</li> <li>a) All b) Some * c) None of:</li> <li>1. Certified copies of the priority documents have been received.</li> <li>2. Certified copies of the priority documents have been received in Application No</li> <li>3. Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).</li> <li>* See the attached detailed Office action for a list of the certified copies not received.</li> </ul>						
2) Notice of (3) Informatio	References Cited (PTO-892) Draftsperson's Patent Drawing Review (PTO- n Disclosure Statement(s) (PTO-1449 or PTO s)/Mail Date		4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	·		

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#### **DETAILED ACTION**

## Response to Arguments

Applicant's arguments, filed 4/21/2006, with respect to claims 1-16 have been fully considered and are persuasive. The final rejection of claims 1-16 has been withdrawn. A new non-final rejection is below.

## Claim Rejections - 35 USC § 103

The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.

Claims 1-5, 8-13, and 16 are rejected under 35 U.S.C. 103(a) as being unpatentable over Musil et al. (US 6,753,538), in view of Chang et al. (US 6,646,259).

Regarding claims 1 and 9, '538 teaches a method for preparing a specimen for application of microanalysis thereto, the method comprising forming an initial conductive layer over only a localized area of interest, without blanket coverage of said initial conductive layer, said initial conductive layer formed through low-energy beam deposition process (Col. 3, II. 65-Col. 4, II. 3, Col. 4, II. 52-65, Col. 5, II. 24, Col. 6, II. 53, Col. 12, II. 48-54). '259 teaches removing a volume of material surrounding the area of interest by forming a pair of trenches in a bulk material having the area of interest formed thereon, thereby forming a membrane including the area of interest sand the initial conductive layer over the area interest, and removing the membrane form the bulk material (Col. 4, II. 7-17). It would have been obvious to form trenches in a bulk material

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thereby forming a membrane and removing the membrane from the bulk material as this is a well-known method of preparing TEM samples.

Regarding claim 2, '538 teaches that the low-energy beam deposition process comprises electron beam deposition (Col. 3, II. 65-Col. 4, II. 3, Col. 4, II. 52-65, Col. 5, II. 24, Col. 6, II. 53, Col. 12, II. 48-54).

Regarding claims 3 and 11, '538 teaches that the conductive later is made of tungsten (Col. 12, II. 48-54).

Regarding claims 4 and 12, '259 teaches that the conductive layer is formed at a thickness of up to 20 nm (Col 3, II. 41-43).

Regarding claims 5 and 13, '259 teaches that the conductive layer is form over an area of about 1 micron by about 10 microns (Col 4, II. 7-12).

Regarding claims 8 and 16, '259 teaches removing a volume of material surrounding the area of interest is implemented by FIB milling (Col. 4, II. 7-12)

Regarding claim 10, '259 teaches that the microanalysis comprises tunneling electron microscopy (Col. 4, II. 7-12).

Claims 6, 7, 14, and 15 are rejected under 35 U.S.C. 103(a) as being unpatentable over Musil et al. (US 6,753,538), in view of Chang et al. (US 6,646,259 B2), further in view of Engelmann et al. (US 6,303,399 B1).

Regarding claims 6, 7, 14, and 15, the aforementioned prior art meets all claim limitation with the exception of implementing high-energy ion beam deposition for thickening the initial conductive layer. '399 teaches implementing high-energy ion beam deposition for the conductive layer (Col. 5, II. 55-59). It would have been obvious to one

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skilled in the art at the time of the invention to implementing high-energy ion beam deposition for thickening the initial conductive layer as this method is faster than low-energy electron beam deposition and is notoriously known in the art.

#### Conclusion

Any inquiry concerning this communication or earlier communications from the examiner should be directed to Jennifer Yantorno whose telephone number is (571) 272-5918. The examiner can normally be reached on Monday-Friday, 9 am - 5 pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, John Lee can be reached on (571) 272-2477. The fax phone number for the organization where this application or proceeding is assigned is 571-273-8300.

Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

JY

JOHN R. LEE SUPERVISORY PATENT EXAMINER TECHNOLOGY CENTER 2800